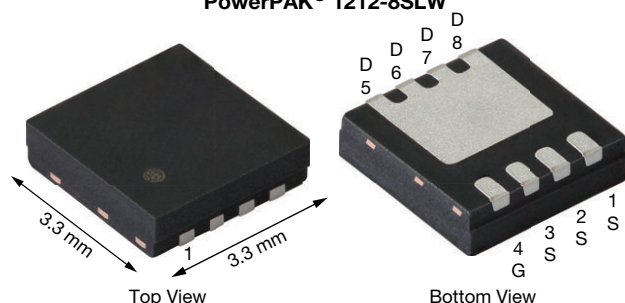


# Automotive N-Channel 80 V (D-S) 175 °C MOSFET

**PowerPAK® 1212-8SLW**

**Marking code:** Q067

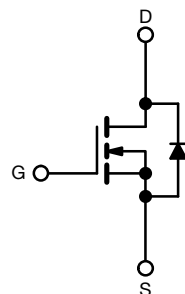
## PRODUCT SUMMARY

|                                               |        |
|-----------------------------------------------|--------|
| $V_{DS}$ (V)                                  | 80     |
| $R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V | 0.0156 |
| $R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V  | 0.0132 |
| $I_D$ (A) <sup>e</sup>                        | 45     |
| Configuration                                 | Single |

## FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 %  $R_g$  and UIS tested
- Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**


N-Channel MOSFET

## ORDERING INFORMATION

|                                 |                                                                                                                              |
|---------------------------------|------------------------------------------------------------------------------------------------------------------------------|
| Package                         | PowerPAK 1212-8SLW                                                                                                           |
| Lead (Pb)-free and halogen-free | SQS182ELNW<br>(for detailed order number please see <a href="http://www.vishay.com/doc?79776">www.vishay.com/doc?79776</a> ) |

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                                 | SYMBOL         | LIMIT       | UNIT |
|-----------------------------------------------------------|----------------|-------------|------|
| Drain-source voltage                                      | $V_{DS}$       | 80          | V    |
| Gate-source voltage                                       | $V_{GS}$       | $\pm 20$    |      |
| Continuous drain current <sup>e</sup>                     | $I_D$          | 45          | A    |
|                                                           |                | 26          |      |
| Continuous source current (diode conduction) <sup>e</sup> | $I_S$          | 59          |      |
| Pulsed drain current <sup>a, e</sup>                      | $I_{DM}$       | 104         |      |
| Single pulse avalanche current                            | $I_{AS}$       | 20          | mJ   |
| Single pulse avalanche energy                             |                | 20          |      |
| Maximum power dissipation <sup>a, e</sup>                 | $P_D$          | 65          | W    |
|                                                           |                | 21          |      |
| Operating junction and storage temperature range          | $T_J, T_{stg}$ | -55 to +175 | °C   |
| Soldering recommendations (peak temperature) <sup>c</sup> |                | 260         |      |

## THERMAL RESISTANCE RATINGS

| PARAMETER                             | SYMBOL     | LIMIT | UNIT |
|---------------------------------------|------------|-------|------|
| Junction-to-ambient                   | $R_{thJA}$ | 54    | °C/W |
| Junction-to-case (drain) <sup>d</sup> | $R_{thJC}$ | 2.3   |      |

## Notes

- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %
- When mounted on 1" square PCB (FR4 material)
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- As per JESD51-14
- Values based on  $R_{thJC}$  and  $T_C$  of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



| SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                      |                                                                                                                        |                                                 |      |        |        |      |
|-----------------------------------------------------------------|----------------------|------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------|------|--------|--------|------|
| PARAMETER                                                       | SYMBOL               | TEST CONDITIONS                                                                                                        |                                                 | MIN. | TYP.   | MAX.   | UNIT |
| Static                                                          |                      |                                                                                                                        |                                                 |      |        |        |      |
| Drain-source breakdown voltage                                  | V <sub>DS</sub>      | V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA                                                                           |                                                 | 80   | -      | -      | V    |
| Gate-source threshold voltage                                   | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                            |                                                 | 1.4  | 1.9    | 2.5    |      |
| Gate-source leakage                                             | I <sub>GSS</sub>     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                        |                                                 | -    | -      | ± 100  | nA   |
| Zero gate voltage drain current                                 | I <sub>DSS</sub>     | V <sub>GS</sub> = 0 V                                                                                                  | V <sub>DS</sub> = 80 V                          | -    | -      | 1      | μA   |
|                                                                 |                      | V <sub>GS</sub> = 0 V                                                                                                  | V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C | -    | -      | 50     |      |
|                                                                 |                      | V <sub>GS</sub> = 0 V                                                                                                  | V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C | -    | -      | 150    |      |
| On-state drain current <sup>a</sup>                             | I <sub>D(on)</sub>   | V <sub>GS</sub> = 10 V                                                                                                 | V <sub>DS</sub> ≥ 5 V                           | 15   | -      | -      | A    |
| Drain-source on-state resistance <sup>a</sup>                   | R <sub>DS(on)</sub>  | V <sub>GS</sub> = 4.5 V                                                                                                | I <sub>D</sub> = 10 A                           | -    | 0.0130 | 0.0156 | Ω    |
|                                                                 |                      | V <sub>GS</sub> = 10 V                                                                                                 | I <sub>D</sub> = 10 A                           | -    | 0.0110 | 0.0132 |      |
|                                                                 |                      | V <sub>GS</sub> = 10 V                                                                                                 | I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C  | -    | -      | 0.0250 |      |
|                                                                 |                      | V <sub>GS</sub> = 10 V                                                                                                 | I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C  | -    | -      | 0.0320 |      |
| Forward transconductance <sup>b</sup>                           | g <sub>fs</sub>      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A                                                                          |                                                 | -    | 65     | -      | S    |
| Dynamic <sup>b</sup>                                            |                      |                                                                                                                        |                                                 |      |        |        |      |
| Input capacitance                                               | C <sub>iss</sub>     | V <sub>GS</sub> = 0 V                                                                                                  | V <sub>DS</sub> = 25 V, f = 1 MHz               | -    | 1457   | 2024   | pF   |
| Output capacitance                                              | C <sub>oss</sub>     |                                                                                                                        |                                                 | -    | 208    | 292    |      |
| Reverse transfer capacitance                                    | C <sub>rss</sub>     |                                                                                                                        |                                                 | -    | 10     | 35     |      |
| Total gate charge <sup>c</sup>                                  | Q <sub>g</sub>       | V <sub>GS</sub> = 10 V                                                                                                 | V <sub>DS</sub> = 40 V, I <sub>D</sub> = 3 A    | -    | 26     | 39     | nC   |
| Gate-source charge <sup>c</sup>                                 | Q <sub>gs</sub>      |                                                                                                                        |                                                 | -    | 5      | -      |      |
| Gate-drain charge <sup>c</sup>                                  | Q <sub>gd</sub>      |                                                                                                                        |                                                 | -    | 5      | -      |      |
| Gate resistance                                                 | R <sub>g</sub>       | f = 1 MHz                                                                                                              |                                                 | 0.4  | 1.0    | 2.0    | Ω    |
| Turn-on delay time <sup>c</sup>                                 | t <sub>d(on)</sub>   | V <sub>DD</sub> = 40 V, R <sub>L</sub> = 13.3 Ω<br>I <sub>D</sub> ≅ 3 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω |                                                 | -    | 10     | 15     | ns   |
| Rise time <sup>c</sup>                                          | t <sub>r</sub>       |                                                                                                                        |                                                 | -    | 4      | 8      |      |
| Turn-off delay time <sup>c</sup>                                | t <sub>d(off)</sub>  |                                                                                                                        |                                                 | -    | 23     | 35     |      |
| Fall time <sup>c</sup>                                          | t <sub>f</sub>       |                                                                                                                        |                                                 | -    | 6      | 9      |      |
| Source-Drain Diode Ratings and Characteristic <sup>b</sup>      |                      |                                                                                                                        |                                                 |      |        |        |      |
| Pulsed current <sup>a</sup>                                     | I <sub>SM</sub>      |                                                                                                                        |                                                 | -    | -      | 175    | A    |
| Forward voltage                                                 | V <sub>SD</sub>      | I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V                                                                           |                                                 | -    | 0.82   | 1.1    | V    |
| Body diode reverse recovery time                                | t <sub>rr</sub>      | V <sub>DD</sub> = 64 V, I <sub>F</sub> = 3.5 A, di/dt = 100 A/μs,<br>R = 10 Ω, L = 0.3 mH, pulse width = 2 μs          |                                                 | -    | 29     | 58     | ns   |
| Body diode reverse recovery charge                              | Q <sub>rr</sub>      |                                                                                                                        |                                                 | -    | 34     | 68     | nC   |
| Reverse recovery fall time                                      | t <sub>a</sub>       |                                                                                                                        |                                                 | -    | 24     | -      |      |
| Reverse recovery rise time                                      | t <sub>b</sub>       |                                                                                                                        |                                                 | -    | 5      | -      | ns   |
| Body diode peak reverse recovery current                        | I <sub>RM(REC)</sub> |                                                                                                                        |                                                 | -    | -2.0   | -      | A    |

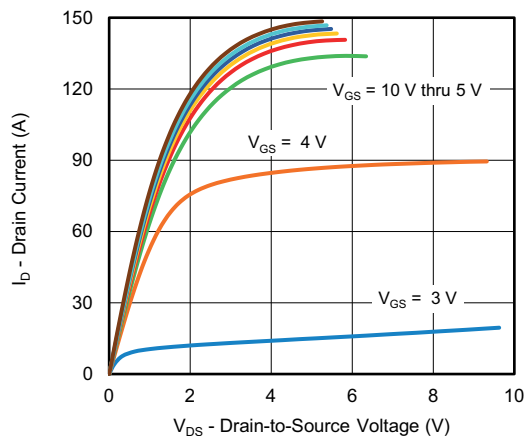
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

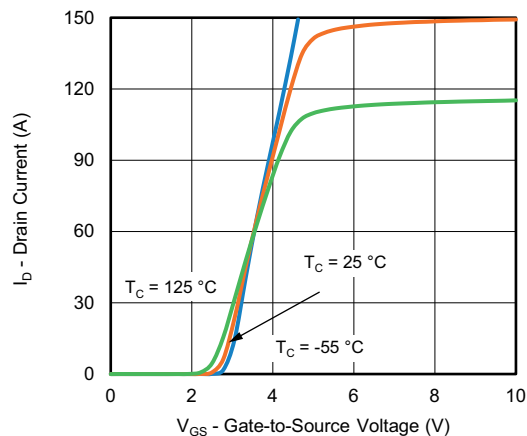
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



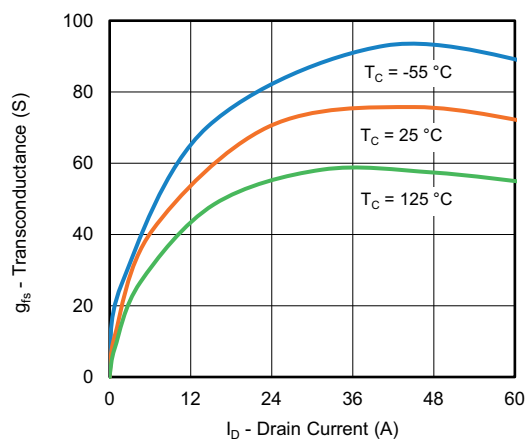
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



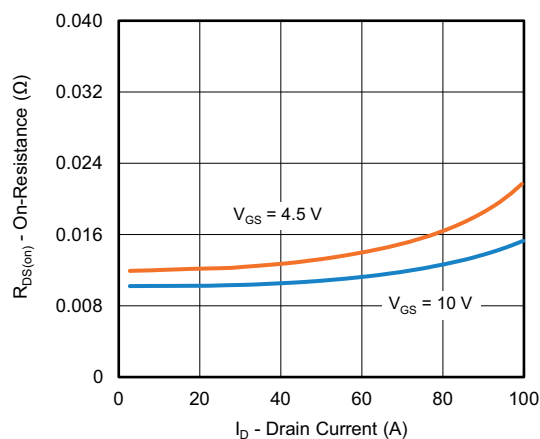
**Output Characteristics**



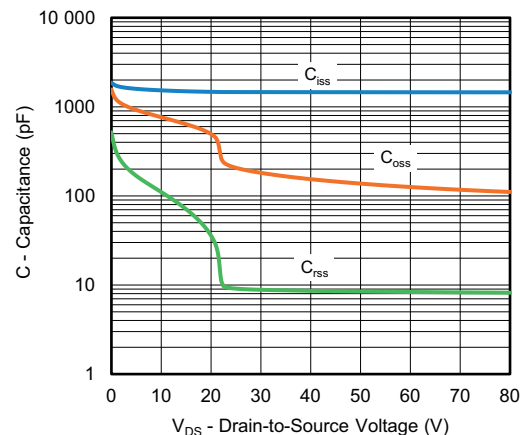
**Transfer Characteristics**



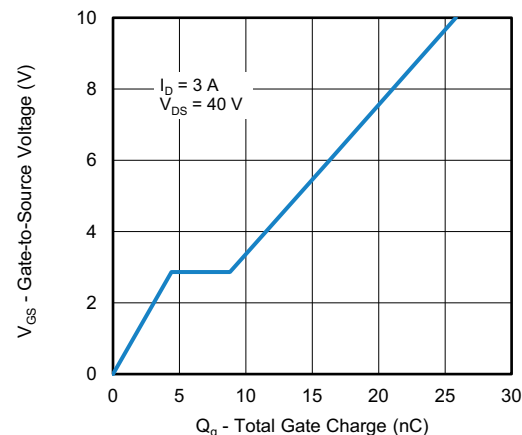
**Transconductance**



**On-Resistance vs. Drain Current**



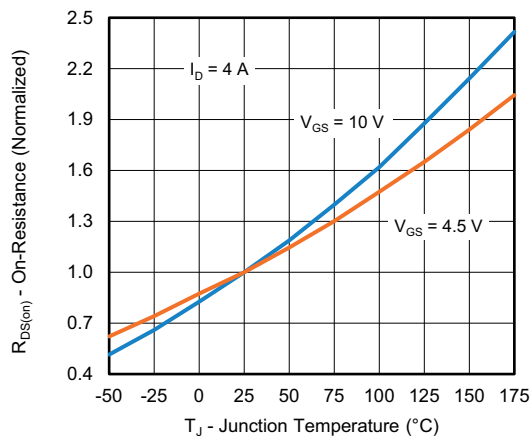
**Capacitance**



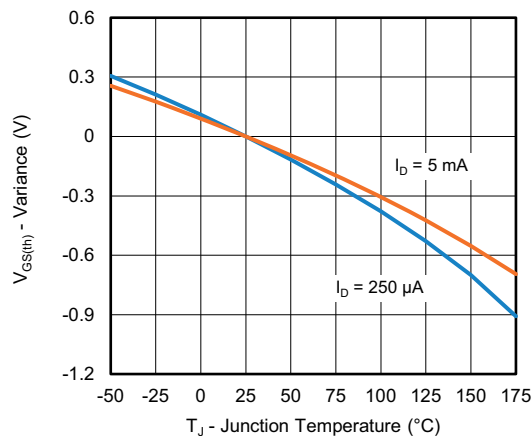
**Gate Charge**



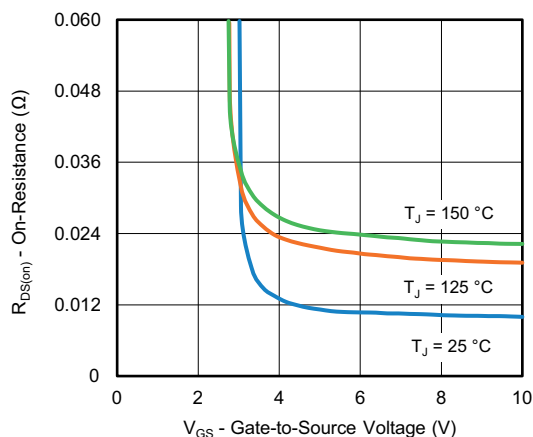
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



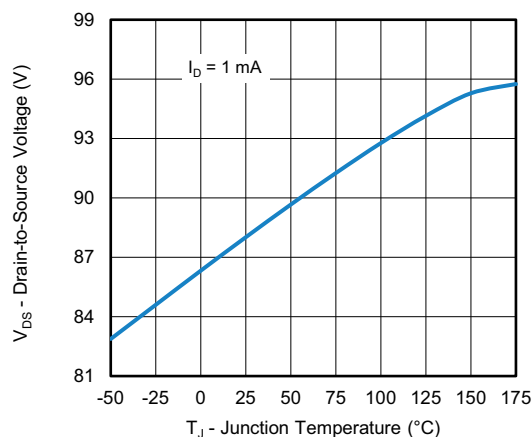
**On-Resistance vs. Junction Temperature**



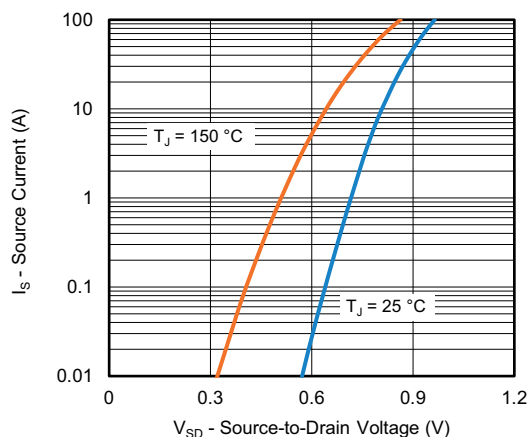
**Threshold Voltage**



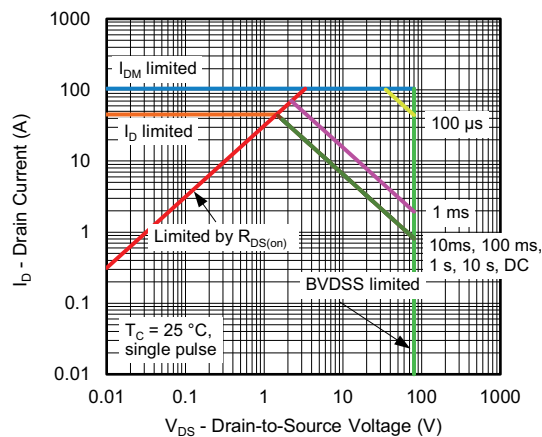
**On-Resistance vs. Gate-to-Source Voltage**



**Drain Source Breakdown vs. Junction Temperature**



**Source Drain Diode Forward Voltage**



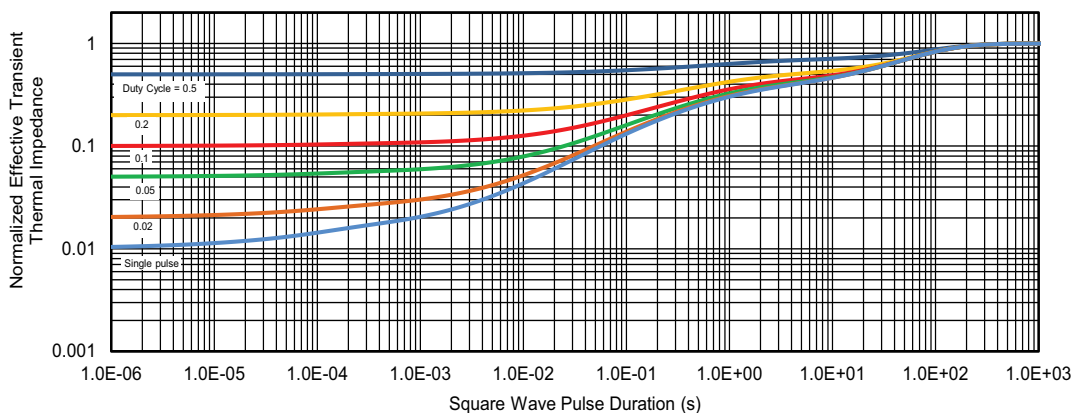
**Safe Operating Area**

**Note**

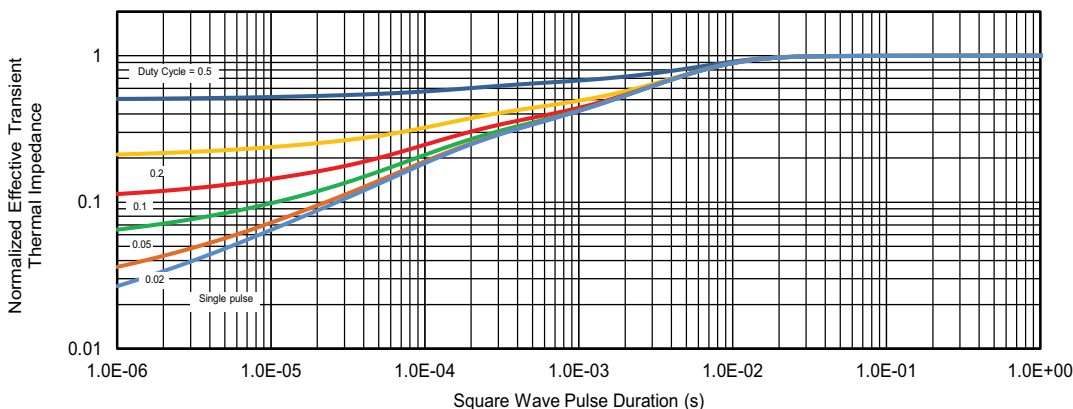
- a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



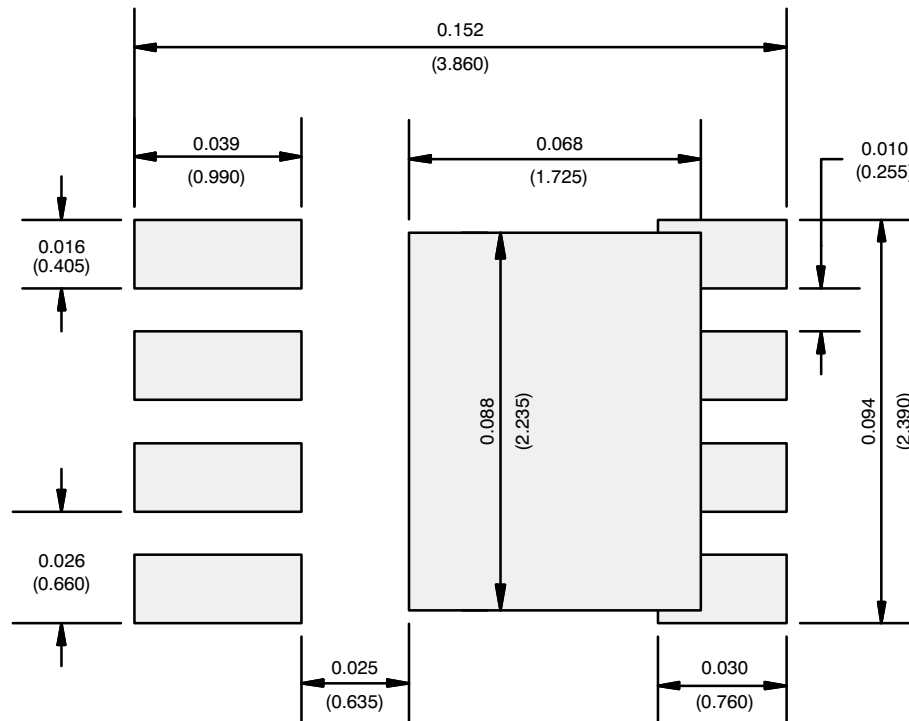
**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^{\circ}\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^{\circ}\text{C}$ )are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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